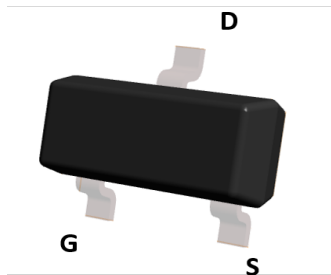
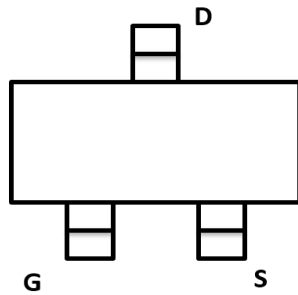


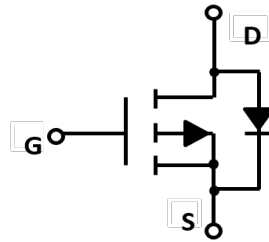
P-Channel Enhancement Mode Field Effect Transistor



Top View



SOT-23-3L



Product Summary

- V_{DS} -30V
- I_D -7.0A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <25mohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <36mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-30	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ\text{C}$ @ Steady State	-7.0
		$T_A=70^\circ\text{C}$ @ Steady State	-5.6
Pulsed Drain Current ^A	I_{DM}	-50	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	1.9	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	65.7	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL07P03AL	F2	3007.	3000	30000	120000	7" reel



YJL07P03AL

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V, T_C=25^\circ\text{C}$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-7.0A$		18.5	25	m Ω
		$V_{GS}=-4.5V, I_D=-5.0A$		24.5	36	
Diode Forward Voltage	V_{SD}	$I_S=-7.0A, V_{GS}=0V$		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I_S				-7.0	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$		1500		pF
Output Capacitance	C_{oss}			178		
Reverse Transfer Capacitance	C_{rss}			146		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=-10V, V_{DS}=-15V, I_D=-6.0A$		28.7		nC
Gate Source Charge	Q_{gs}			5.5		
Gate Drain Charge	Q_{gd}			5.4		
Reverse Recovery Charge	Q_{rr}	$I_F=-9A, di/dt=500A/\mu s$		6.0		ns
Reverse Recovery Time	t_{rr}			14		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-10V, V_{DS}=-15V, I_D=-6.0A, R_{GEN}=2.5\Omega$		10		ns
Turn-on Rise Time	t_r			44		
Turn-off Delay Time	$t_{D(off)}$			54		
Turn-off Fall Time	t_f			59		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JL}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

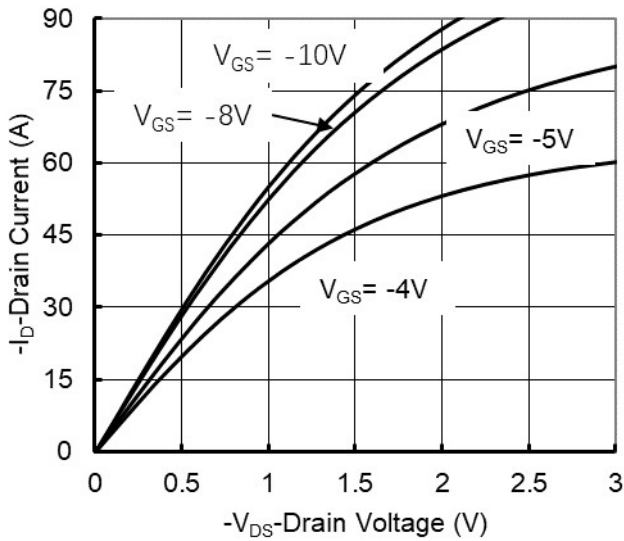


Figure 1. Output Characteristics

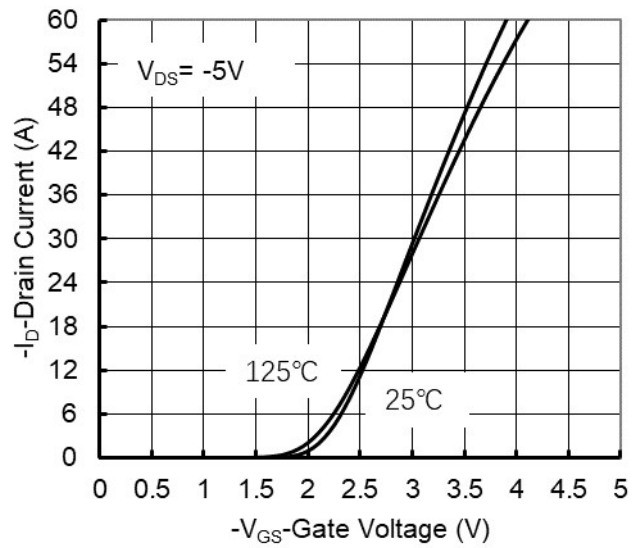


Figure 2. Transfer Characteristics

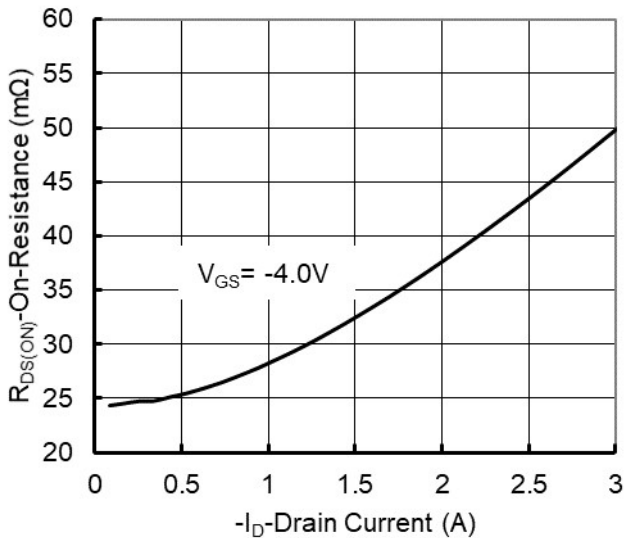


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

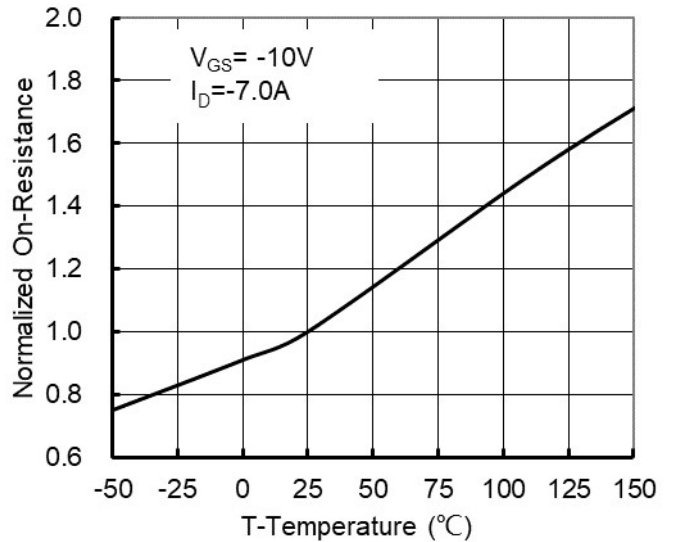


Figure 4. On-Resistance vs. Junction Temperature

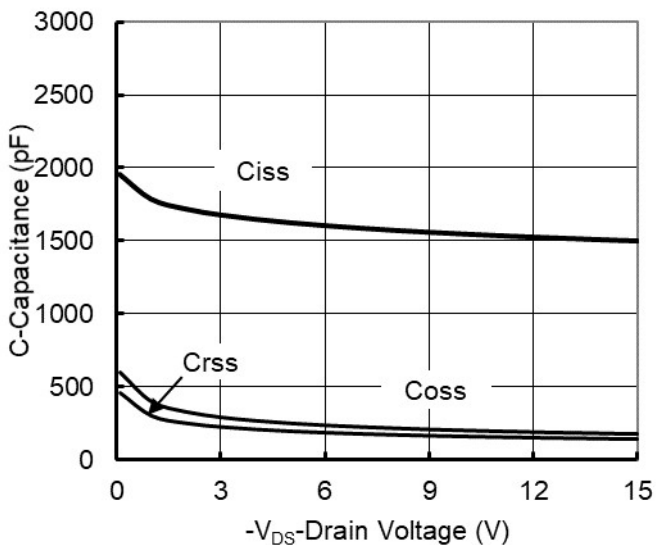


Figure 5. Capacitance Characteristics

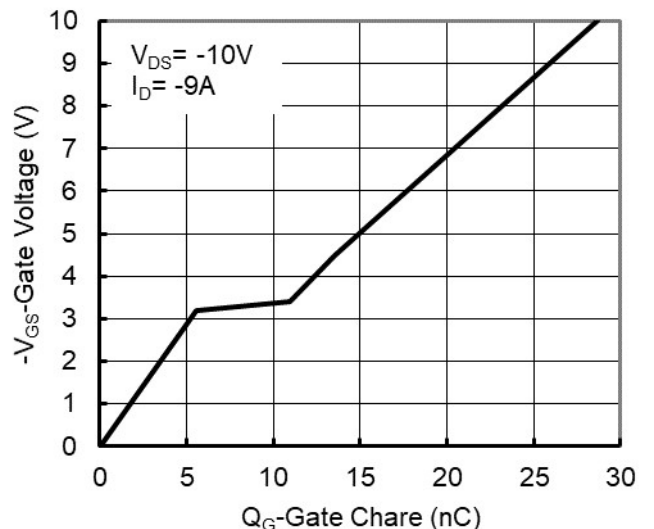


Figure 6. Gate Charge

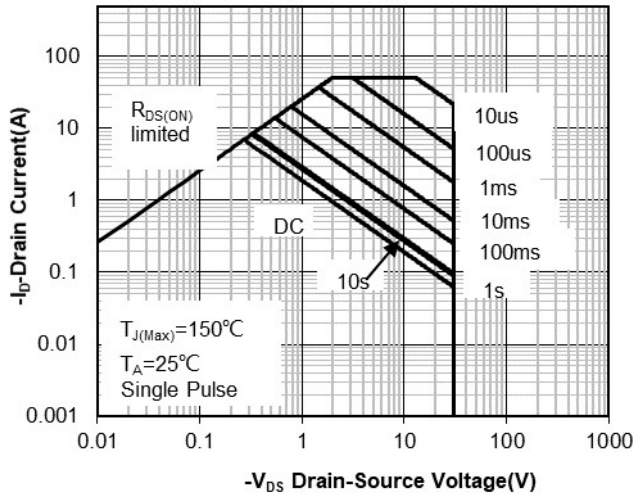


Figure 7. Safe Operation Area

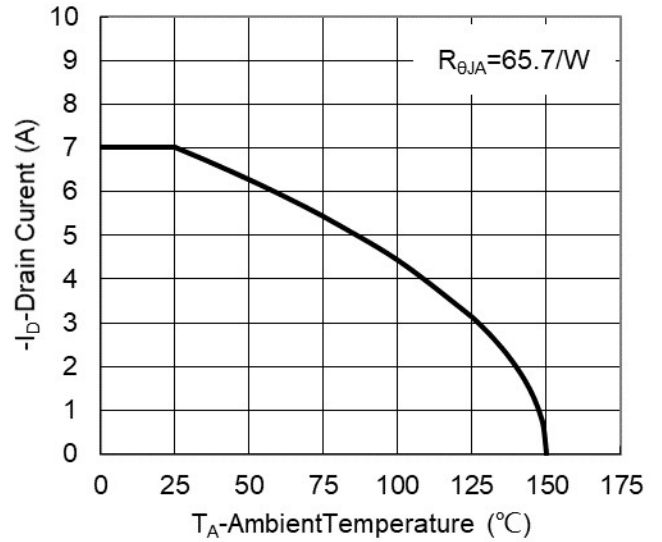


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

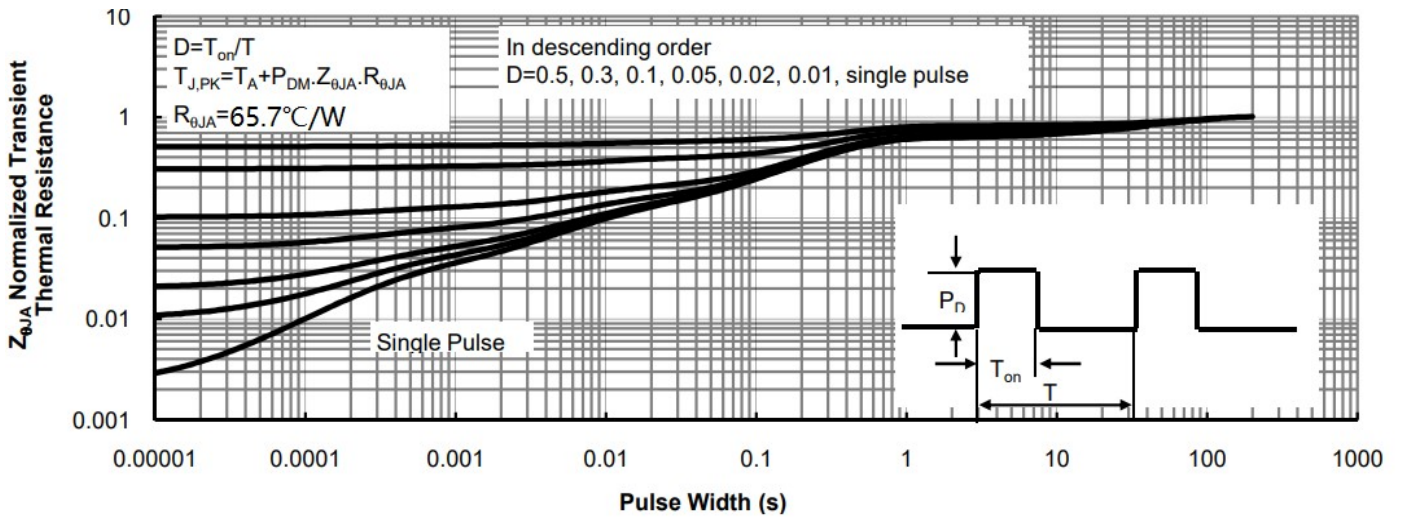


Figure 9. Normalized Maximum Transient Thermal Impedance



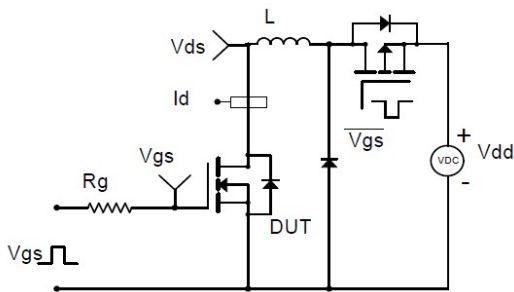
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



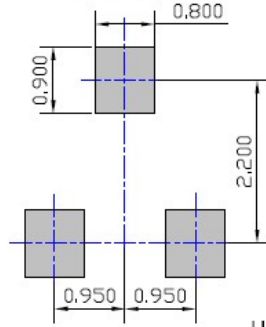
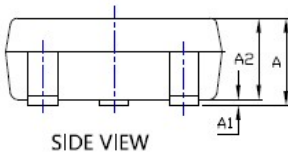
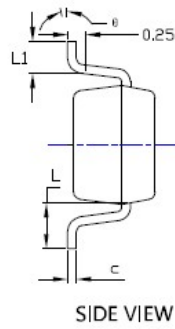
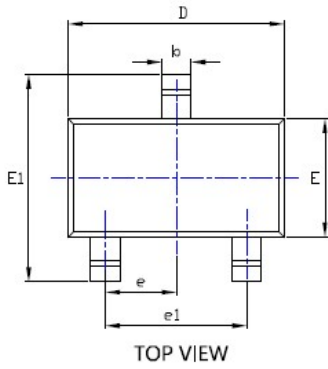
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



■ SOP-23-3L Package information



UNIT: mm

SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.041	---	0.049	1.050	---	1.250
A1	0.000	---	0.008	0.000	---	0.200
A2	0.041	0.043	0.045	1.050	1.100	1.150
b	0.012	0.016	0.020	0.300	0.400	0.500
c	0.004	---	0.008	0.100	---	0.200
D	0.111	0.115	0.119	2.820	2.920	3.020
E	0.059	0.063	0.067	1.500	1.600	1.700
E1	0.104	0.110	0.116	2.650	2.800	2.950
e	0.037TYP			0.950TYP		
e1	0.071	0.075	0.079	1.800	1.900	2.000
L	0.024REF			0.600REF		
L1	0.012	0.018	0.240	0.300	0.450	0.600
ø	0*	---	8*	0*	---	8*

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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